

**isc N-Channel MOSFET Transistor**
**BUK456-800A/B**
**DESCRIPTION**

- Drain Source Voltage-  
:  $V_{DSS}=800V(\text{Min})$
- LOW  $R_{DS(\text{ON})}$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

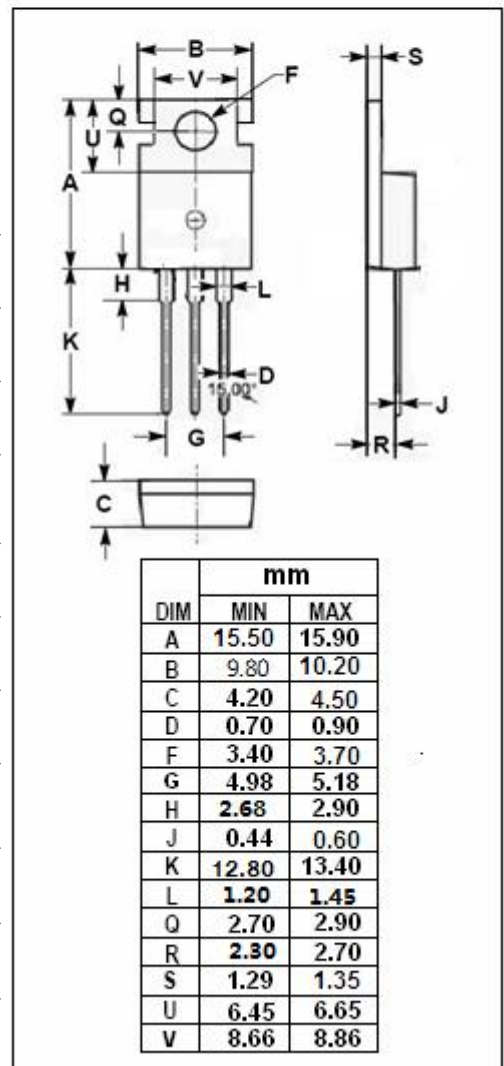
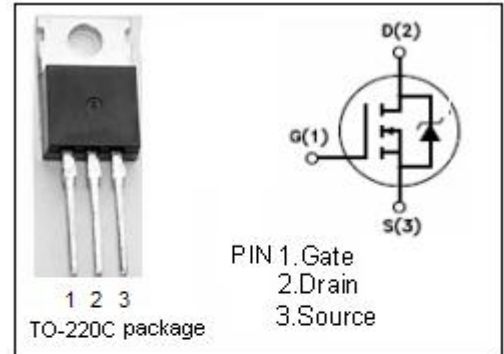
- Designed for Switched Mode Power Supplies (SMPS), motor control, welding, and in general purpose switching resistance application

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	800	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous @ $TC=25^\circ\text{C}$	BUK456-800A	4
		BUK456-800B	3.5
$P_{tot}$	Total Dissipation @ $TC=25^\circ\text{C}$	125	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C}/\text{W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	60	$^\circ\text{C}/\text{W}$



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**• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 0.25mA	800			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.1		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =1.5A	BUK456-800A		3.0	Ω
			BUK456-800B		4.0	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =800V; V <sub>GS</sub> = 0			20	uA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>F</sub> =4.0A; V <sub>GS</sub> =0			1.3	V
G <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> = 25V; I <sub>D</sub> =1.5A	3.0			S
t <sub>r</sub>	Rise time	V <sub>GS</sub> =10V; I <sub>D</sub> =2.3A; R <sub>GS</sub> =50 Ω		50	70	ns
t <sub>on</sub>	Turn-on time			10	25	ns
t <sub>f</sub>	Fall time			40	60	ns
t <sub>off</sub>	Turn-off time			130	150	ns

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